



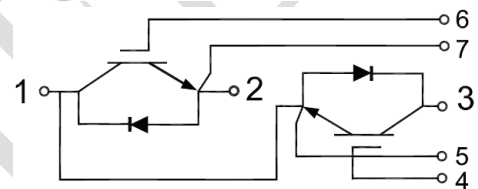
# GT150HF170T2VH

## IGBT Module

Preliminary Data

### Features:

- Short Circuit Rated  $>10\mu\text{s}$
- Low Saturation Voltage:  $V_{CE(sat)} = 2.30\text{V}$  @  $I_C = 150\text{A}$ ,  $T_C = 25^\circ\text{C}$
- Low Switching Loss
- 100% RBSOA Tested ( $2 \times I_C$ )
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



### Applications:

- Industrial Inverters
- Motor Drives
- UPS Systems

### IGBT, Inverter

Maximum Rated Values ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

$V_{CES}$	Collector-Emitter Blocking Voltage		1700	V
$V_{GES}$	Gate-Emitter Voltage		$\pm 20$	V
$I_C$	Continuous Collector Current	$T_C = 80^\circ\text{C}$	150	A
		$T_C = 25^\circ\text{C}$	190	A
$I_{CM}$	Peak Collector Current Repetitive	$T_J = 150^\circ\text{C}$	300	A
$t_{SC}$	Short Circuit Withstand Time		$>10$	$\mu\text{s}$
$P_D$	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ\text{C}$ $T_{Jmax} = 150^\circ\text{C}$	880	W



## Electrical Characteristics of IGBT ( $T_C=25^\circ\text{C}$ unless otherwise specified)

### Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1 \text{ mA}, V_{CE} = V_{GE}$	5.5	6.0	6.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150\text{A}, V_{GE} = 15\text{V}$	$T_J = 25^\circ\text{C}$	2.30	2.50	V
			$T_J = 125^\circ\text{C}$	2.70		V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$			1	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}, T_J = 25^\circ\text{C}$			400	nA
$C_{ies}$	Input Capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		10.2		nF
$C_{oes}$	Output Capacitance			0.54		nF

### Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 900\text{V}, I_C = 150\text{A}, R_G = 10\Omega, V_{GE} = \pm 15\text{V},$ Inductive Load	$T_J = 25^\circ\text{C}$	410		ns
			$T_J = 125^\circ\text{C}$	410		
$t_r$	Rise Time		$T_J = 25^\circ\text{C}$	150		ns
			$T_J = 125^\circ\text{C}$	150		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^\circ\text{C}$	365		ns
			$T_J = 125^\circ\text{C}$	400		
$t_f$	Fall Time		$T_J = 25^\circ\text{C}$	250		ns
			$T_J = 125^\circ\text{C}$	370		
$E_{on}$	Turn-on Switching Loss		$T_J = 25^\circ\text{C}$	53.6		mJ
			$T_J = 125^\circ\text{C}$	63.3		
$E_{off}$	Turn-off Switching Loss	$T_J = 25^\circ\text{C}$	23.1		mJ	
		$T_J = 125^\circ\text{C}$	38.0			
$Q_g$	Total Gate Charge	$T_J = 25^\circ\text{C}$	870		nC	
RBSOA	RBSOA	$I_C=300\text{A}, V_{CC}=1650\text{V}, V_p=1700\text{V}, R_g = 10\Omega, V_{GE}=\pm 15\text{V to } 0\text{V}, T_J = 150^\circ\text{C}$	Trapezoid			
SCSOA	SCSOA	$V_{CC} = 900\text{V}, V_{GE} = 15\text{V}, T_J = 150^\circ\text{C}$	10		$\mu\text{s}$	
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case			0.142	$^\circ\text{C/W}$	



## Diode, Inverter

### Maximum Rated Values( $T_C=25^{\circ}\text{C}$ unless otherwise specified)

$V_{RRM}$	Repetitive Peak Reverse Voltage	1700	V
$I_F$	Diode Continuous Forward Current	150	A
$I_{FM}$	Peak FWD Current Repetitive	300	A

### Electrical Characteristics of FWD( $T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{FM}$	Forward Voltage	$I_F = 150\text{A}$ , $V_{GE} = 0\text{V}$	$T_J = 25^{\circ}\text{C}$	1.70		V
			$T_J = 125^{\circ}\text{C}$	1.90		
$I_{rr}$	Peak Reverse Recovery Current	$I_F = 150\text{A}$ , $di/dt = 1080\text{A}/\mu\text{s}$ , $V_{rr} = 900\text{V}$ , $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	95		A
			$T_J = 125^{\circ}\text{C}$	125		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 150\text{A}$ , $di/dt = 1080\text{A}/\mu\text{s}$ , $V_{rr} = 900\text{V}$ , $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	32.2		$\mu\text{C}$
			$T_J = 125^{\circ}\text{C}$	53.7		
$E_{rec}$	Reverse Recovery Energy	$I_F = 150\text{A}$ , $di/dt = 1080\text{A}/\mu\text{s}$ , $V_{rr} = 900\text{V}$ , $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	17.6		mJ
			$T_J = 125^{\circ}\text{C}$	31.2		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case			0.233		$^{\circ}\text{C}/\text{W}$

## Module

Symbol	Description	Min	Typ	Max	Unit
$V_{iso}$	Isolation Voltage (All Terminals Shorted)	$f = 50\text{Hz}$ , 1minute	2500		V
$T_J$	Maximum Junction Temperature			150	$^{\circ}\text{C}$
$T_{JOP}$	Maximum Operating Junction Temperature Range		-40 +150		$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature		-40 +125		$^{\circ}\text{C}$
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)		0.03		$^{\circ}\text{C}/\text{W}$
M	Power Terminals Screw:M6		3.0	5.0	N·m
M	Mounting Screw:M6		4.0	6.0	N·m
G	Weight		300		g

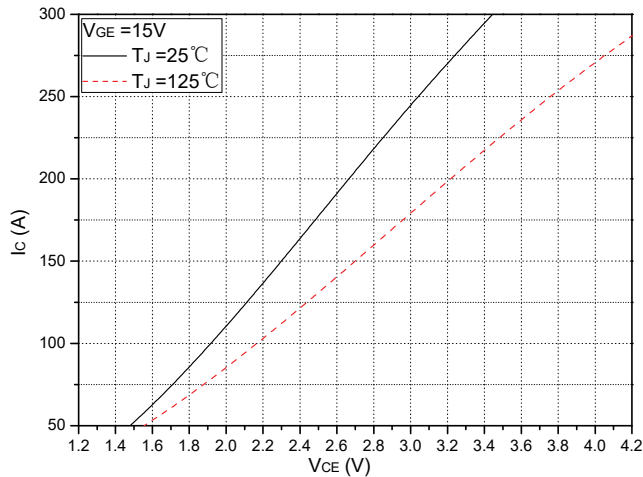


Fig.1 Typical Saturation Voltage Characteristics

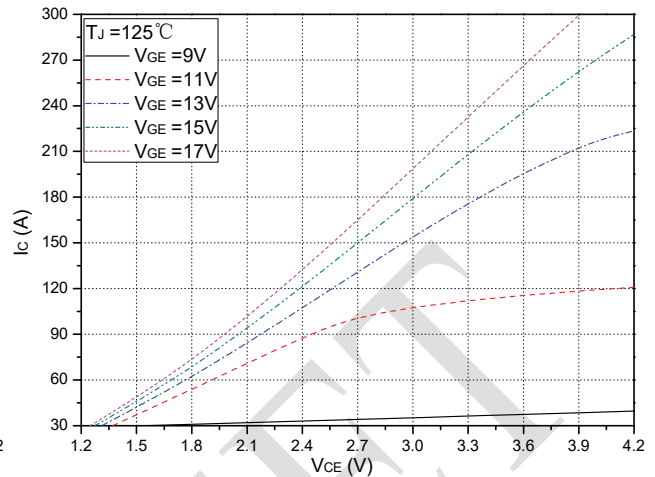


Fig.2 Typical Output Characteristics

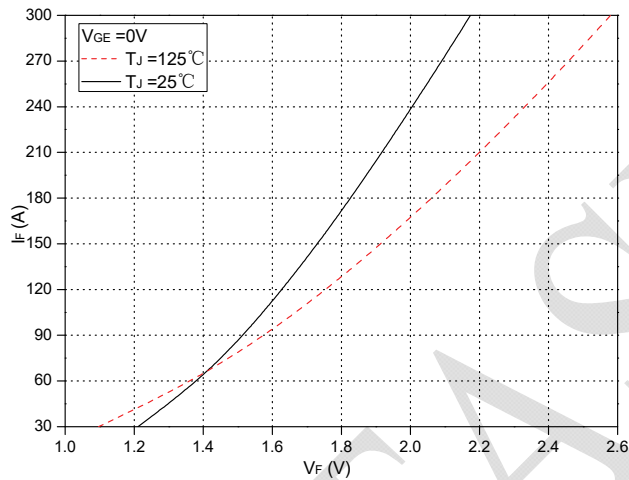


Fig.3 Forward Characteristics of FWD

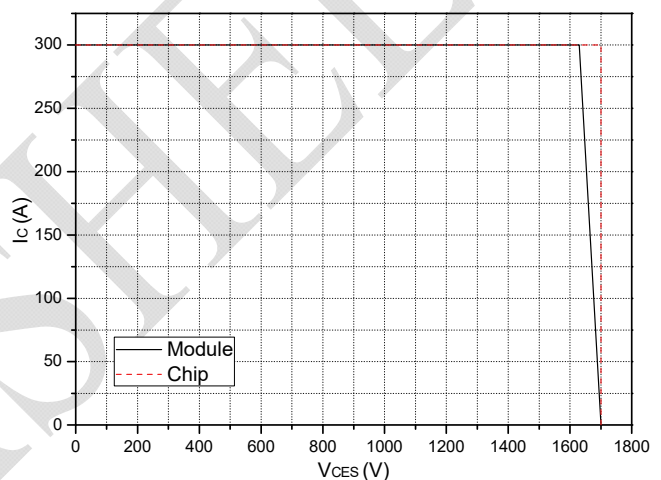


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

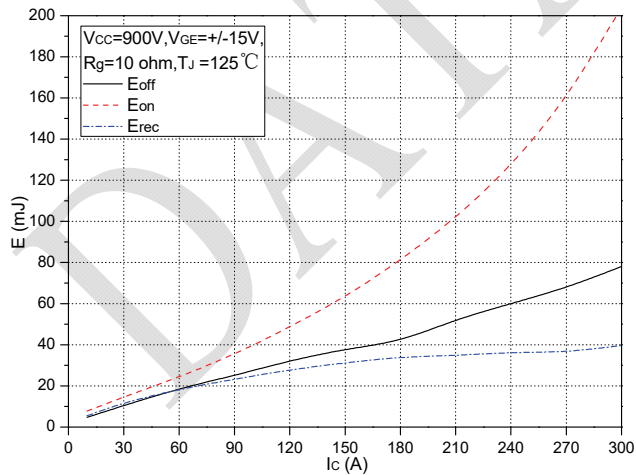


Fig.5 Typical Switching Loss vs. Collector Current

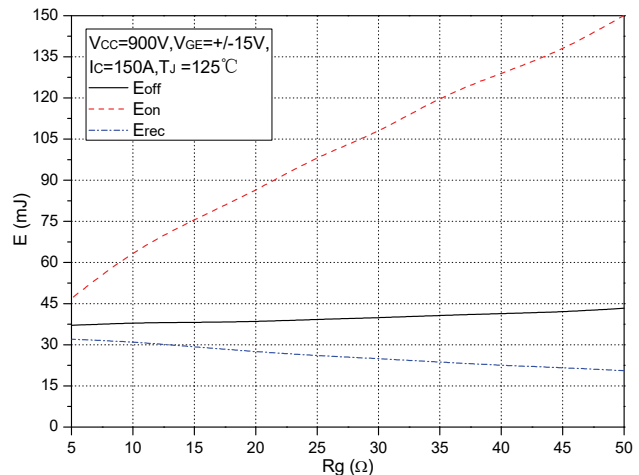


Fig.6 Typical Switching Loss vs. Gate Resistance

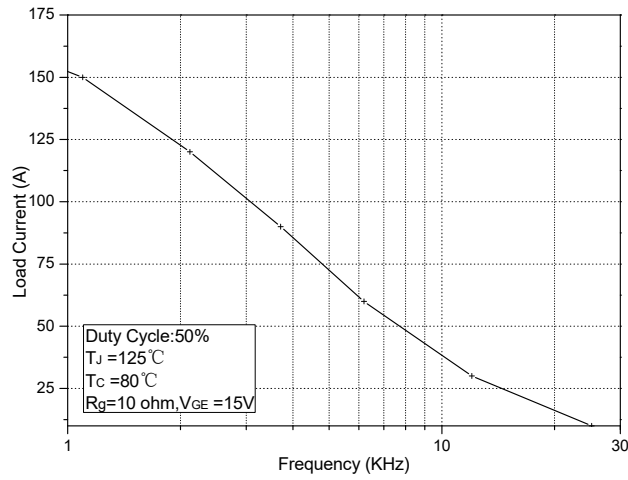


Fig.7 Typical Load Current vs. Frequency

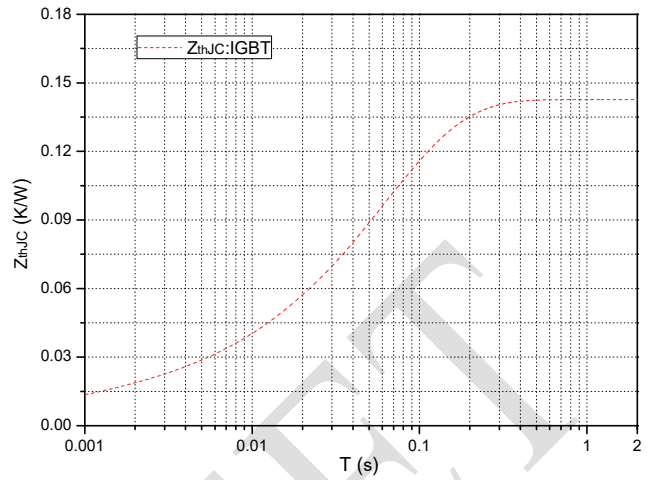


Fig.8 Transient Thermal Impedance (IGBT)

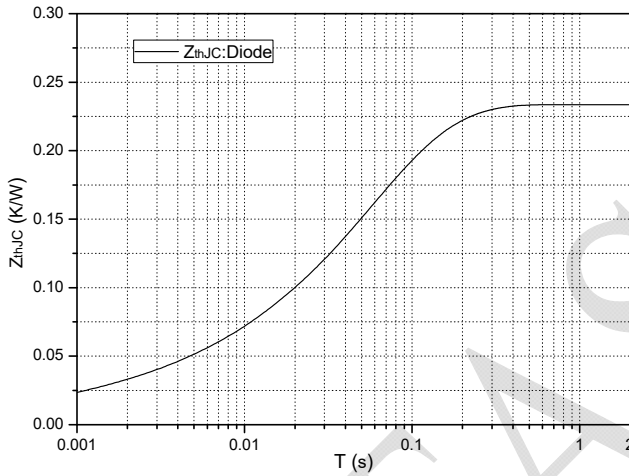


Fig.9 Transient Thermal Impedance (Diode)

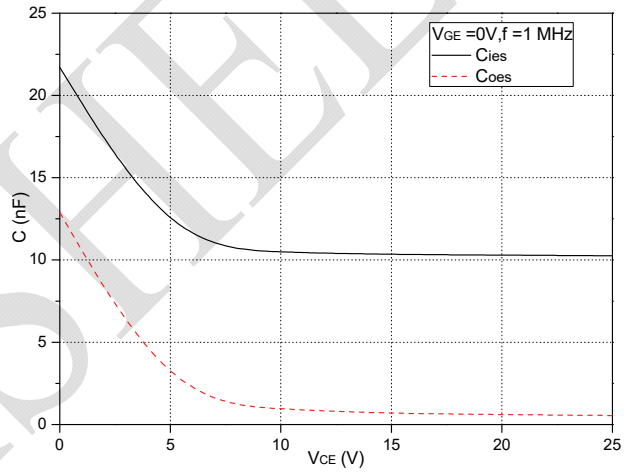


Fig.10 Capacitance Characteristics





Date	Revision	Notes
12/08/2020	01	Initial Release

### **Announcement**

Information in this document is believed to be accurate and reliable. However, NJSME does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

### **Right to Make Changes**

NJSME reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

DATA SHEET